

Patrick Kung

List of Publications by Year in descending order

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167
papers

4,888
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81743

39
h-index

102304

66
g-index

167
all docs

167
docs citations

167
times ranked

4121
citing authors

#	ARTICLE	IF	CITATIONS
1	High quality AlN and GaN epilayers grown on (000̄...1) sapphire, (100), and (111) silicon substrates. Applied Physics Letters, 1995, 66, 2958-2960.	1.5	175
2	High-speed, low-noise metal-semiconductor-metal ultraviolet photodetectors based on GaN. Applied Physics Letters, 1999, 74, 762-764.	1.5	175
3	AlGaIn ultraviolet photoconductors grown on sapphire. Applied Physics Letters, 1996, 68, 2100-2101.	1.5	171
4	Electroluminescence at 375nm from a ZnO-GaN:Mg-Al ₂ O ₃ heterojunction light emitting diode. Applied Physics Letters, 2006, 88, 1419-18.	1.5	170
5	Solar-blind AlGaIn photodiodes with very low cutoff wavelength. Applied Physics Letters, 2000, 76, 403-405.	1.5	166
6	High-power 280 nm AlGaIn light-emitting diodes based on an asymmetric single-quantum well. Applied Physics Letters, 2004, 84, 1046-1048.	1.5	165
7	High-quality visible-blind AlGaIn p-i-n photodiodes. Applied Physics Letters, 1999, 74, 1171-1173.	1.5	145
8	4.5 mW operation of AlGaIn-based 267 nm deep-ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4701-4703.	1.5	124
9	High quantum efficiency AlGaIn solar-blind p-i-n photodiodes. Applied Physics Letters, 2004, 84, 1248-1250.	1.5	121
10	Determination of the band-gap energy of Al _{1-x} In _x N grown by metal-organic chemical-vapor deposition. Applied Physics Letters, 1997, 71, 800-802.	1.5	119
11	Al _x Ga _{1-x} N (0 ≤ x ≤ 1) ultraviolet photodetectors grown on sapphire by metal-organic chemical-vapor deposition. Applied Physics Letters, 1997, 70, 949-951.	1.5	113
12	Visible blind GaN p-i-n photodiodes. Applied Physics Letters, 1998, 72, 3303-3305.	1.5	112
13	Al Ga _{1-x} N for solar-blind UV detectors. Journal of Crystal Growth, 2001, 231, 366-370.	0.7	106
14	A crystallographic model of (000̄...1) aluminum nitride epitaxial thin film growth on (000̄...1) sapphire substrate. Journal of Applied Physics, 1994, 75, 3964-3967.	1.1	104
15	High quality aluminum nitride epitaxial layers grown on sapphire substrates. Applied Physics Letters, 1994, 64, 339-341.	1.5	100
16	Hole-initiated multiplication in back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 90, 1411-12.	1.5	95
17	Avalanche multiplication in AlGaIn based solar-blind photodetectors. Applied Physics Letters, 2005, 87, 2411-23.	1.5	93
18	Top-emission ultraviolet light-emitting diodes with peak emission at 280 nm. Applied Physics Letters, 2002, 81, 801-802.	1.5	91

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19	Growth of Al _x Ga _{1-x} N:Ge on sapphire and silicon substrates. Applied Physics Letters, 1995, 67, 1745-1747.	1.5	90
20	Thermal stability of GaN thin films grown on (0001) Al ₂ O ₃ , (011 $\bar{1}$,2) Al ₂ O ₃ and (0001)Si ₆ H ₆ SiC substrates. Journal of Applied Physics, 1994, 76, 236-241.	1.1	89
21	Crystallography of epitaxial growth of wurtzite-type thin films on sapphire substrates. Journal of Applied Physics, 1994, 75, 4515-4519.	1.1	89
22	Band-gap narrowing and potential fluctuation in Si-doped GaN. Applied Physics Letters, 1999, 74, 102-104.	1.5	88
23	Photovoltaic effects in GaN structures with p-n junctions. Applied Physics Letters, 1995, 67, 2028-2030.	1.5	78
24	Kinetics of photoconductivity in n-type GaN photodetector. Applied Physics Letters, 1995, 67, 3792-3794.	1.5	77
25	Lateral epitaxial overgrowth of GaN films on sapphire and silicon substrates. Applied Physics Letters, 1999, 74, 570-572.	1.5	73
26	Photoluminescence study of AlGa _N -based 280 nm ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4083-4085.	1.5	72
27	Metalorganic chemical vapor deposition of monocrystalline GaN thin films on LiGaO ₂ substrates. Applied Physics Letters, 1996, 69, 2116-2118.	1.5	67
28	320Å–256 solar-blind focal plane arrays based on Al _x Ga _{1-x} N. Applied Physics Letters, 2005, 86, 011117.	1.5	66
29	Pulse autocorrelation measurements based on two- and three-photon conductivity in a GaN photodiode. Applied Physics Letters, 1999, 75, 3778-3780.	1.5	62
30	Aluminum gallium nitride short-period superlattices doped with magnesium. Applied Physics Letters, 1999, 74, 2023-2025.	1.5	57
31	Comparison of ultraviolet light-emitting diodes with peak emission at 340 nm grown on GaN substrate and sapphire. Applied Physics Letters, 2002, 81, 2151-2153.	1.5	56
32	Plasmon-Induced Transparency by Hybridizing Concentric-Twisted Double Split Ring Resonators. Scientific Reports, 2015, 5, 15735.	1.6	56
33	Fabrication of GaN nanotubular material using MOCVD with an aluminium oxide membrane. Nanotechnology, 2006, 17, 54-59.	1.3	52
34	A Facile Electrochemical Reduction Method for Improving Photocatalytic Performance of Fe ₂ O ₃ Photoanode for Solar Water Splitting. ACS Applied Materials & Interfaces, 2017, 9, 381-390.	4.0	51
35	Design and analysis of perfect terahertz metamaterial absorber by a novel dynamic circuit model. Optics Express, 2013, 21, 16455.	1.7	46
36	Polarization-Dependent, Frequency-Selective THz Stereometamaterial Perfect Absorber. Physical Review Applied, 2014, 1, .	1.5	44

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37	Monolayer MoS ₂ field-effect transistors patterned by photolithography for active matrix pixels in organic light-emitting diodes. Npj 2D Materials and Applications, 2019, 3, .	3.9	43
38	Eu ²⁺ →Mn ²⁺ energy transfer in white-light-emitting T-phase (Ba,Ca) ₂ SiO ₄ :Eu ²⁺ , Mn ²⁺ phosphor. Journal of Luminescence, 2010, 130, 560-566.	1.5	42
39	Comparison of trimethylgallium and triethylgallium for the growth of GaN. Applied Physics Letters, 1997, 71, 3272-3274.	1.5	41
40	Geiger-mode operation of back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 91, .	1.5	40
41	Equivalent-Circuit Interpretation of the Polarization Insensitive Performance of THz Metamaterial Absorbers. IEEE Transactions on Terahertz Science and Technology, 2013, 3, 846-850.	2.0	40
42	GaNN/GaN Multi-Quantum Well Laser Diodes Grown by Low-Pressure Metalorganic Chemical Vapor Deposition. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	38
43	Effect of pressure and Al doping on structural and optical properties of ZnO nanowires synthesized by chemical vapor deposition. Journal of Luminescence, 2014, 146, 470-474.	1.5	37
44	Investigating the Redox Properties of Two-Dimensional MoS ₂ Using Photoluminescence Spectroelectrochemistry and Scanning Electrochemical Cell Microscopy. Journal of Physical Chemistry Letters, 2020, 11, 3488-3494.	2.1	35
45	Scaling in back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 91, .	1.5	33
46	Synthesis of MoS ₂ from [Mo ₃ S ₇ (S ₂ CNEt ₂) ₃]I for enhancing photoelectrochemical performance and stability of Cu ₂ O photocathode toward efficient solar water splitting. Journal of Materials Chemistry A, 2018, 6, 9569-9582.	5.2	33
47	Photoluminescence enhancement of monolayer MoS ₂ using plasmonic gallium nanoparticles. Nanoscale Advances, 2019, 1, 884-893.	2.2	33
48	Breast cancer biomarker detection through the photoluminescence of epitaxial monolayer MoS ₂ flakes. Scientific Reports, 2020, 10, 16039.	1.6	33
49	Phase-matched optical second-harmonic generation in GaN and AlN slab waveguides. Journal of Applied Physics, 1999, 85, 2497-2501.	1.1	31
50	Future of Al _x Ga _{1-x} N materials and device technology for ultraviolet photodetectors. , 2002, , .		31
51	Review on Polarization Selective Terahertz Metamaterials: from Chiral Metamaterials to Stereometamaterials. Journal of Infrared, Millimeter, and Terahertz Waves, 2017, 38, 1047-1066.	1.2	28
52	Strong Solar Radiation Forces from Anomalously Reflecting Metasurfaces for Solar Sail Attitude Control. Scientific Reports, 2018, 8, 10026.	1.6	27
53	Impact of Substrate and Bright Resonances on Group Velocity in Metamaterial without Dark Resonator. Scientific Reports, 2015, 5, 14373.	1.6	26
54	Growth of GaN without Yellow Luminescence. Materials Research Society Symposia Proceedings, 1995, 395, 625.	0.1	25

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55	Atom Probe Tomography of Zinc Oxide Nanowires. <i>Journal of Electronic Materials</i> , 2012, 41, 801-808.	1.0	24
56	Characteristics of THz carrier dynamics in GaN thin film and ZnO nanowires by temperature dependent terahertz time domain spectroscopy measurement. <i>Solid-State Electronics</i> , 2012, 78, 68-74.	0.8	23
57	Photoluminescence Study of GaN. <i>Acta Physica Polonica A</i> , 1995, 88, 601-606.	0.2	22
58	Characteristics of high-quality p-type Al _x Ga _{1-x} N/GaN superlattices. <i>Applied Physics Letters</i> , 2002, 80, 2108-2110.	1.5	21
59	ZnO thin film templates for GaN-based devices. , 2005, , .		21
60	Surface optical phonons in GaAs nanowires grown by Ga-assisted chemical beam epitaxy. <i>Journal of Applied Physics</i> , 2014, 115, 034307.	1.1	20
61	Observation of room temperature surface-emitting stimulated emission from GaN:Ge by optical pumping. <i>Journal of Applied Physics</i> , 1996, 80, 6544-6546.	1.1	18
62	Thermally stable deep-blue Ba _{1.2} Ca _{0.8} SiO ₄ :Ce ³⁺ phosphor for white-light-emitting diode. <i>Journal of Luminescence</i> , 2010, 130, 1292-1294.	1.5	18
63	Enhanced fabrication process of zinc oxide nanowires for optoelectronics. <i>Thin Solid Films</i> , 2014, 555, 42-47.	0.8	18
64	Investigation of robust flexible conformal THz perfect metamaterial absorber. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	18
65	High-quantum-efficiency solar-blind photodetectors. , 2004, , .		17
66	White-light generation through Ce ³⁺ /Mn ²⁺ -codoped and Eu ²⁺ -doped Ba _{1.2} Ca _{0.8} SiO ₄ T-phase phosphors. <i>Journal of Luminescence</i> , 2010, 130, 2442-2445.	1.5	17
67	Investigation of tunable terahertz metamaterial perfect absorber with anisotropic dielectric liquid crystal. <i>AIP Advances</i> , 2017, 7, .	0.6	17
68	Investigations of p-type signal for ZnO thin films grown on (100) GaAs substrates by pulsed laser deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1038-1041.	0.8	16
69	Conducting properties of nearly depleted ZnO nanowire UV sensors fabricated by dielectrophoresis. <i>Nanotechnology</i> , 2013, 24, 415702.	1.3	16
70	Al _x Ga _{1-x} N-Based Materials and Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 1996, 449, 79.	0.1	15
71	Materials characterization of n - ZnO / p - GaN : Mg / c - Al ₂ O ₃ UV LEDs grown by pulsed laser deposition and metal-organic chemical vapor deposition. <i>Superlattices and Microstructures</i> , 2007, 42, 322-326.	1.4	15
72	Temperature and excitation power-resistant white-light emission of the -phase phosphor. <i>Solid State Communications</i> , 2010, 150, 329-332.	0.9	14

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73	$\text{Al}_x\text{Ga}_{1-x}\text{N}$ materials and device technology for solar blind ultraviolet photodetector applications. , 2001, .		13
74	Pure zinblende GaAs nanowires grown by Ga-assisted chemical beam epitaxy. Journal of Crystal Growth, 2013, 372, 205-212.	0.7	13
75	Exciton-exciton scattering in vapor phase ZnO nanoparticles. Applied Physics Letters, 2015, 106, .	1.5	13
76	Thickness identification of epitaxial Bi_2Te_3 via optical contrast. 2D Materials, 2016, 3, 021010.	2.0	13
77	Ultra-High Efficiency and Broad Band Operation of Infrared Metasurface Anomalous Reflector based on Graphene Plasmonics. Scientific Reports, 2019, 9, 1249.	1.6	13
78	Forbidden and Second-Order Phonons in Raman Spectra of Single and Few-Layer MoS ₂ Close to C Exciton Resonance. Journal of Physical Chemistry C, 2021, 125, 23904-23910.	1.5	13
79	Observation of inversion layers at AlN-Si interfaces fabricated by metal organic chemical vapour deposition. Electronics Letters, 1996, 32, 1622.	0.5	12
80	Lateral epitaxial overgrowth of GaN on sapphire and silicon substrates for ultraviolet photodetector applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 107-112.	1.7	12
81	Direct Measurement of Band Edge Discontinuity in Individual Core-Shell Nanowires by Photocurrent Spectroscopy. Nano Letters, 2013, 13, 4152-4157.	4.5	12
82	Observation of Hydrofluoric Acid Burns on Osseous Tissues by Means of Terahertz Spectroscopic Imaging. IEEE Transactions on Terahertz Science and Technology, 2013, 3, 387-394.	2.0	12
83	Comprehensive study of terahertz metamaterial absorber by applying a hybrid approach on its circuit analogue. Optical Materials Express, 2015, 5, 1772.	1.6	12
84	Al doping in ZnO nanowires enhances ultraviolet emission and suppresses broad defect emission. Journal of Luminescence, 2019, 211, 264-270.	1.5	12
85	Growth, doping, and characterization of ZnO nanowire arrays. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, .	0.6	11
86	Terahertz metamaterials perfect absorbers for sensing and imaging. Proceedings of SPIE, 2013, , .	0.8	11
87	Solar-blind $\text{Al}_x\text{Ga}_{1-x}\text{N}$ p-i-n photodetectors grown on LEO and non-LEO GaN. , 2000, 3948, 265.		10
88	New Green Phosphor $(\text{Ba}_{1.2}\text{Ca}_{0.8-x}\text{Eu}_x)\text{SiO}_4$ for White-Light-Emitting Diode. Japanese Journal of Applied Physics, 2010, 49, 020214.	0.8	10
89	Observation of Hydrofluoric Acid Burns on Osseous Tissues by Means of Terahertz Spectroscopic Imaging. IEEE Journal of Biomedical and Health Informatics, 2013, 17, 798-805.	3.9	10
90	Atom probe tomography of AlInN/GaN HEMT structures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, .	0.6	10

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91	Structural and mechanical characterization of carbon fibers grown by laser induced chemical vapor deposition at hyperbaric pressures. Carbon, 2020, 162, 95-105.	5.4	10
92	Analytical simulation of RBS spectra of nanowire samples. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 116-120.	0.6	9
93	Nanoscale Raman Characterization of a 2D Semiconductor Lateral Heterostructure Interface. ACS Nano, 2022, 16, 340-350.	7.3	9
94	<title>GaN p-i-n photodiodes with high visible-to-ultraviolet rejection ratio</title>. , 1998, 3287, 214.		8
95	Review of III-nitride optoelectronic materials for light emission and detection. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, S141-S148.	0.8	8
96	Back-illuminated solar-blind photodetectors for imaging applications. , 2005, 5732, 175.		8
97	Low Leakage Current ZnO Nanowire Schottky Photodiodes Built by Dielectrophoretic Contact. IEEE Electron Device Letters, 2015, 36, 814-816.	2.2	8
98	High Resolution X-ray Diffraction of GaN Grown on Sapphire Substrates. Materials Research Society Symposia Proceedings, 1996, 449, 477.	0.1	7
99	III-nitride avalanche photodiodes. , 2007, , .		7
100	Morphology of twinned GaN grown on (11 $\bar{1}$ 0) sapphire substrates. Solid-State Electronics, 1997, 41, 227-229.	0.8	6
101	Schottky MSM photodetectors on GaN films grown on sapphire by lateral epitaxial overgrowth. , 1999, , .		6
102	Electrodeposited Transition Metal Dichalcogenides for Use in Hydrogen Evolution Electrocatalysts. Journal of the Electrochemical Society, 2022, 169, 026510.	1.3	6
103	High sensitivity and high selectivity terahertz biomedical imaging (Invited Paper). Chinese Optics Letters, 2011, 9, 110009-110012.	1.3	5
104	High Efficient THz Emission From Unbiased and Biased Semiconductor Nanowires Fabricated Using Electron Beam Lithography. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-7.	1.9	5
105	MOCVD growth of high quality GaN -- AlGa N based structures on Al O_3 substrates with dislocation density less than 10^7cm^{-2} . Journal of the European Ceramic Society, 1997, 17, 1781-1785.	2.8	4
106	Nanoscale characteristics of single crystal zinc oxide nanowires. , 2011, , .		4
107	(Invited) Transition Metal Dichalcogenide Semiconductor Growth and Large Area Devices for Optoelectronics and Sensing. ECS Transactions, 2017, 80, 1-11.	0.3	4
108	Theoretical Analysis of the Nanoscale Composition, Tip-Enhanced Raman Spectroscopy, and Electronic Properties of Alloys in 2D MoS -- WS -- Heterostructures. Journal of Physical Chemistry C, 2022, 126, 9099-9108.	1.5	4

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109	Spectral Response of GaN P-N Junction Photovoltaic Structures. Materials Research Society Symposia Proceedings, 1995, 395, 955.	0.1	3
110	The Rise of III-nitrides: An Introduction. , 2005, , 9-22.		3
111	Design, simulation, and characterization of THz metamaterial absorber. , 2012, , .		3
112	Comparative reconstructions of THz spectroscopic imaging for non-destructive testing and biomedical imaging. , 2012, , .		3
113	Theoretical and experimental investigation of hybrid broadband terahertz metamaterial absorber. Proceedings of SPIE, 2013, , .	0.8	3
114	Investigation of silicon-germanium nanowires THz emission. , 2014, , .		3
115	Continuous-flow system and monitoring tools for the dielectrophoretic integration of nanowires in light sensor arrays. Nanotechnology, 2015, 26, 115502.	1.3	3
116	Continuous-wave room-temperature operation of InGaN/GaN multiquantum well lasers grown by low-pressure metalorganic chemical vapor deposition. , 1998, , .		2
117	Etching of ZnO towards the development of ZnO homostructure LEDs. , 2007, , .		2
118	Acquisition and analysis of Terahertz Time Domain imaging and sensing. , 2010, , .		2
119	Design, simulation, and characterization of THz metamaterial absorber. , 2011, , .		2
120	InP/ZnS core-shell quantum dots sensitized ZnO nanowires for photovoltaic devices. , 2011, , .		2
121	Effects of saline on terahertz absorption of aqueous glucose at physiological concentrations probed by THz spectroscopy. , 2013, , .		2
122	Identification of tissue interaction of terahertz radiation toward functional tissue imaging by terahertz spectroscopic imaging. , 2013, , .		2
123	Polarization controllable THz stereometamaterial absorber. , 2014, , .		2
124	Polarization dependent trion dynamics in large area CVD grown 2D monolayer MoS2 by terahertz time-domain spectroscopy. Journal Physics D: Applied Physics, 2019, 52, 155104.	1.3	2
125	Nanotechnology in Electronics. , 2014, , 17-36.		2
126	<title>Recent advances in III-nitride materials, characterization and device applications</title>. , 1997, , .		1

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127	Growth of deep-UV light-emitting diodes by metalorganic chemical vapor deposition. , 2004, , .		1
128	Solar-blind avalanche photodiodes. , 2006, , .		1
129	Blue-emitting Sr ₃ Ga ₂ O ₅ Cl ₂ :Eu ²⁺ +phosphor for white-light-emitting diode. , 2010, , .		1
130	Excellent Brightness with Shortening Lifetime of Textured Zn ₂ SiO ₄ :Mn ²⁺ +Phosphor Films on Quartz Glass. Japanese Journal of Applied Physics, 2010, 49, 042603.	0.8	1
131	Application of terahertz spectral imaging for the identification of osseous tissue. , 2011, , .		1
132	Temperature dependent THz time-domain spectroscopy of carrier dynamics in GaN thin film. , 2011, , .		1
133	High Resolution, Two-Dimensional Image Mapping of ZnO Nanowires by Confocal MicroPhotoluminescence and MicroRaman Spectroscopy. Journal of Nanoscience and Nanotechnology, 2011, 11, 5898-5903.	0.9	1
134	Identification of tissue interaction of terahertz radiation toward functional tissue imaging. , 2013, , .		1
135	Investigation of high frequency carrier dynamics of Al-doped ZnO nanowires by terahertz time domain spectroscopy. , 2014, , .		1
136	THz emission from InP and InGaAs nanowires fabricated using electron beam lithography. , 2015, , .		1
137	Spectroscopic Characteristics of Three Dimensional Split-Ring Resonator Arrays at Terahertz Frequencies. Journal of Nanoscience and Nanotechnology, 2015, 15, 2289-2293.	0.9	1
138	Liquid Crystal Frequency Tunable Terahertz Metamaterial Absorber. , 2016, , .		1
139	Morphological characterization of selectively overgrown GaN via lateral epitaxy. Journal of Materials Science, 2002, 37, 1951-1957.	1.7	0
140	Short-wavelength ultraviolet light-emitting diodes based on AlGaIn. , 2005, , .		0
141	AlGaIn-based deep UV light emitting diodes with peak emission below 255 nm. , 2005, , .		0
142	Fabrication of GaN nanotubular material using MOCVD with aluminum oxide membrane. , 2006, 6127, 123.		0
143	Optical Properties of Closely Coupled Dilute Nitride Mid-Infrared InNSb Quantum Dots. , 2008, , .		0
144	Super-bright and short-lived photoluminescence of textured Zn ₂ SiO ₄ :Mn ²⁺ +phosphor film on quartz glass. , 2010, , .		0

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145	White-light generation through Ce ³⁺ /Mn ²⁺ -codoped and Eu ²⁺ -doped Ba _{1.2} Ca _{0.8} SiO ₄ T-phase phosphors. , 2010, , .		0
146	Synthesis and Optical Properties of ZnO Nanowires for Nanophotonics. , 2010, , .		0
147	Synthesis and optical properties of ZnO nanowires for nanophotonics. , 2010, , .		0
148	Terahertz spectroscopic properties of three-dimensional split-ring resonator arrays. , 2011, , .		0
149	Quantum dot functionalized ZnO nanowire/P3HT hybrid photovoltaic devices. , 2011, , .		0
150	Hybrid nanostructures based on quantum dots and nanowires. , 2011, , .		0
151	Photovoltaic devices based on quantum dot functionalized nanowire arrays embedded in an organic matrix. Proceedings of SPIE, 2012, , .	0.8	0
152	Highly efficient, polarization insensitive terahertz metamaterial perfect absorber and imaging. , 2012, , .		0
153	Aperture-less terahertz near-field imaging. Proceedings of SPIE, 2013, , .	0.8	0
154	Analysis of terahertz metamaterial perfect absorber by using a novel quasi-static RLC circuit model. , 2013, , .		0
155	Voltage and Laser-Assisted Mode Atom Probe Tomography of Gallium Nitride. Microscopy and Microanalysis, 2013, 19, 990-991.	0.2	0
156	Synthesis and Optical Properties of Undoped and Aluminum Doped ZnO Nanowires for Optoelectronic Nanodevice Applications. , 2014, , .		0
157	Slow light by hybridized concentric-twisted double split ring resonators and THz application. , 2015, , .		0
158	Independent component analysis applications on THz sensing and imaging. , 2016, , .		0
159	Biased THz emission from InGaAs nanowires fabricated using electron beam lithography. , 2016, , .		0
160	Slowing terahertz wave using thin flexible metamaterials. , 2016, , .		0
161	Terahertz metamaterials: design, implementation, modeling and applications. Proceedings of SPIE, 2016, , .	0.8	0
162	Terahertz devices, spectroscopy, and signal processing for biosensing. Proceedings of SPIE, 2016, , .	0.8	0

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163	Electrically Tunable THz Polarization Conversion in Liquid Crystal Metamaterials. , 2018, , .		0
164	Observation of Broadband Electrically Tunable THz Metamaterials Polarization Conversion. , 2019, , .		0
165	In Situ Thermomechanical Loading for TEM Studies of Nanocrystalline Alloys. Microscopy and Microanalysis, 2021, 27, 2420-2424.	0.2	0
166	Highly Efficient, Polarization Insensitive Terahertz Metamaterial Perfect Absorber and Imaging. , 2012, , .		0
167	Slow Light by Hybridized Double Split Ring Resonators. , 2016, , .		0